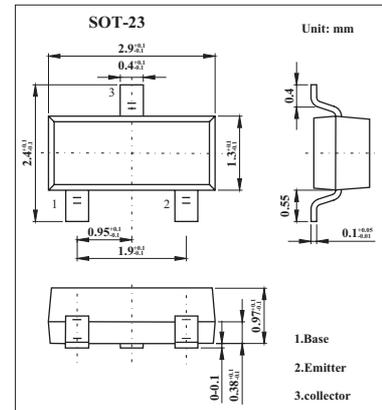


## NPN Switching Transistor

## BSV52

## ■ Features

- High current (max. 100 mA).
- Low voltage (max. 12 V).

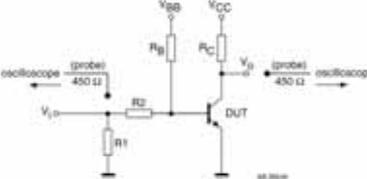
■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	20	V
Collector-emitter voltage	$V_{CE0}$	12	V
Emitter-base voltage	$V_{EB0}$	5	V
Collector current	$I_C$	100	mA
Peak collector current	$I_{CM}$	200	mA
Peak base current	$I_{BM}$	100	mA
Total power dissipation	$P_{tot}$	250	mW
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating ambient temperature	$R_{amb}$	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th\ j-a}$	500	K/W

\* Transistor mounted on an FR4 printed-circuit board.

## BSV52

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector cutoff current	I <sub>CBO</sub>	I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V			400	nA	
		I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 125 °C			30	μA	
Emitter cutoff current	I <sub>EBO</sub>	I <sub>C</sub> = 0; V <sub>EB</sub> = 4 V			100	nA	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 10 mA	40		120		
collector-emitter saturation voltage	V <sub>CEsat</sub>	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 300 μA			300	mV	
		I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA			250	mV	
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA			400	mV	
base-emitter saturation voltage	V <sub>BEsat</sub>	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	700		850	mV	
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA			1.4	V	
Collector capacitance	C <sub>c</sub>	I <sub>E</sub> = I <sub>C</sub> = 0; V <sub>CB</sub> = 5 V; f = 1 MHz			4	pF	
Emitter capacitance	C <sub>e</sub>	I <sub>C</sub> = I <sub>E</sub> = 0; V <sub>EB</sub> = 1 V; f = 1 MHz			4.5	pF	
Transition frequency	f <sub>T</sub>	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	400	500		MHz	
Turn-on time	t <sub>on</sub>	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 3 mA; I <sub>Boff</sub> = -1.5 mA			10	ns	
Delay time	t <sub>d</sub>				4	ns	
Rise time	t <sub>r</sub>					6	ns
Turn-off time	t <sub>off</sub>					20	ns
Storage time	t <sub>s</sub>		V <sub>i</sub> = 0.5 V to 4.2 V; T = 500 μs; t <sub>b</sub> = 10 μs; t <sub>f</sub> = t <sub>s</sub> ≤ 3 ns. R <sub>1</sub> = 56 Ω; R <sub>2</sub> = 1 kΩ; R <sub>B</sub> = 1 kΩ; R <sub>C</sub> = 270 Ω.			10	ns
Fall time	t <sub>f</sub>		V <sub>BB</sub> = 0.2 V; V <sub>CC</sub> = 2.7 V. Oscilloscope: input impedance Z <sub>i</sub> = 50 Ω.			10	ns

## ■ Marking

Marking	B2
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